



(51) International Patent Classification:

G06N 20/10 (2019.01) G01N 21/88 (2006.01)

G06N 3/08 (2006.01) G01N 21/95 (2006.01)

(21) International Application Number:

PCT/US2019/068219

(22) International Filing Date:

23 December 2019 (23.12.2019)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

62/787,549 02 January 2019 (02.01.2019) US

(71) Applicant: **KLA CORPORATION** [US/US]; Legal Department, One Technology Drive, Milpitas, California 95035 (US).

(72) Inventors: **OPHIR, Boaz**; 3 HaRofe St., 3436702 Haifa (IL). **ODES, Yehuda**; Yehuda Odes, Borochoy 21, 2820138 Kiryat Ata (IL). **SHUSTERMAN, Udi**; Kibbutz Ramat David, 3658700 Ramat Rachel (IL).

(74) Agent: **MCANDREWS, Kevin et al.**; KLA CORPORATION, Legal Department, One Technology Drive, Milpitas, California 95035 (US).

(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IR, IS, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

(54) Title: MACHINE LEARNING FOR METROLOGY MEASUREMENTS

200

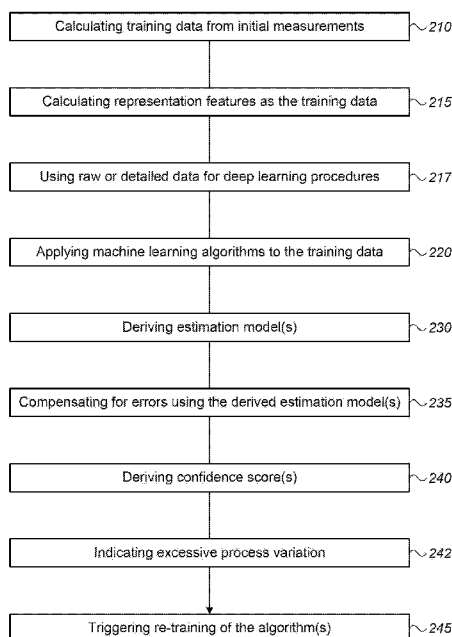


Figure 2

(57) Abstract: Metrology methods, modules and systems are provided, for using machine learning algorithms to improve the metrology accuracy and the overall process throughput. Methods comprise calculating training data concerning metrology metric(s) from initial metrology measurements, applying machine learning algorithm(s) to the calculated training data to derive an estimation model of the metrology metric(s), deriving measurement data from images of sites on received wafers, and using the estimation model to provide estimations of the metrology metric(s) with respect to the measurement data. While the training data may use two images per site, in operation a single image per site may suffice - reducing the measurement time to less than half the current measurement time. Moreover, confidence score(s) may be derived as an additional metrology and process control, and deep learning may be used to enhance the accuracy and/or speed of the metrology module.

Published:

- *with international search report (Art. 21(3))*
- *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments (Rule 48.2(h))*

MACHINE LEARNING FOR METROLOGY MEASUREMENTS

CROSS REFERENCE TO RELATED APPLICATIONS

[0001] This application claims the benefit of U.S. Provisional Patent Application No. 62/787549 filed on January 2, 2019, which is incorporated herein by reference in its entirety.

BACKGROUND OF THE INVENTION

1. TECHNICAL FIELD

[0002] The present invention relates to the field of semiconductor metrology, and more particularly, to implementation of machine learning in the metrology measurement process.

2. DISCUSSION OF RELATED ART

[0003] Typical metrology measurements of targets on wafer site estimate the overlay between target structures in images of the targets, usually for two images per target (0° and 180°-rotated images) to achieve good accuracy.

SUMMARY OF THE INVENTION

[0004] The following is a simplified summary providing an initial understanding of the invention. The summary does not necessarily identify key elements nor limit the scope of the invention, but merely serves as an introduction to the following description.

[0005] One aspect of the present invention provides a method comprising calculating training data concerning at least one metrology metric from initial metrology measurements, applying at least one machine learning algorithm to the calculated training data to derive an estimation model of the at least one metrology metric, deriving measurement data from images of sites on received wafers, and using the estimation model to provide estimations of the at least one metrology metric with respect to the measurement data.

[0006] These, additional, and/or other aspects and/or advantages of the present invention are set forth in the detailed description which follows; possibly inferable from the detailed description; and/or learnable by practice of the present invention.

BRIEF DESCRIPTION OF THE DRAWINGS

[0007] For a better understanding of embodiments of the invention and to show how the same may be carried into effect, reference will now be made, purely by way of example, to the accompanying drawings in which like numerals designate corresponding elements or sections throughout.

[0008] In the accompanying drawings:

[0009] **Figure 1** is a high-level schematic block diagram and illustration of a system with a metrology module, according to some embodiments of the invention.

[0010] **Figure 2** is a high-level flowchart illustrating a method, according to some embodiments of the invention.

DETAILED DESCRIPTION OF THE INVENTION

[0011] In the following description, various aspects of the present invention are described. For purposes of explanation, specific configurations and details are set forth in order to provide a thorough understanding of the present invention. However, it will also be apparent to one skilled in the art that the present invention may be practiced without the specific details presented herein. Furthermore, well known features may have been omitted or simplified in order not to obscure the present invention. With specific reference to the drawings, it is stressed that the particulars shown are by way of example and for purposes of illustrative discussion of the present invention only, and are presented in the cause of providing what is believed to be the most useful and readily understood description of the principles and conceptual aspects of the invention. In this regard, no attempt is made to show structural details of the invention in more detail than is necessary for a fundamental understanding of the invention, the description taken with the drawings making apparent to those skilled in the art how the several forms of the invention may be embodied in practice.

[0012] Before at least one embodiment of the invention is explained in detail, it is to be understood that the invention is not limited in its application to the details of construction and the arrangement of the components set forth in the following description or illustrated in the drawings. The invention is applicable to other embodiments that may be practiced

or carried out in various ways as well as to combinations of the disclosed embodiments. Also, it is to be understood that the phraseology and terminology employed herein are for the purpose of description and should not be regarded as limiting.

[0013] Unless specifically stated otherwise, as apparent from the following discussions, it is appreciated that throughout the specification discussions utilizing terms such as "processing", "computing", "calculating", "determining", "enhancing", "deriving" or the like, refer to the action and/or processes of a computer or computing system, or similar electronic computing device, that manipulates and/or transforms data represented as physical, such as electronic, quantities within the computing system's registers and/or memories into other data similarly represented as physical quantities within the computing system's memories, registers or other such information storage, transmission or display devices. In certain embodiments, illumination technology may comprise, electromagnetic radiation in the visual range, ultraviolet or even shorter wave radiation such as x rays, and possibly even particle beams.

[0014] Embodiments of the present invention provide efficient and economical methods and mechanisms for implementing metrology measurements in semiconductor production processes and thereby provide improvements to the technological field of semiconductor metrology. Metrology methods, modules and systems are provided, for using machine learning algorithms to improve the metrology accuracy and the overall process throughput. Methods comprise calculating training data concerning metrology metric(s) from initial metrology measurements, applying machine learning algorithm(s) to the calculated training data to derive an estimation model of the metrology metric(s), deriving measurement data from images of sites on received wafers, and using the estimation model to provide estimations of the metrology metric(s) with respect to the measurement data. While the training data may use two images per site, in operation a single image per site may suffice – reducing the measurement time to less than half the current measurement time. Moreover, confidence score(s) may be derived as an additional metrology and process control, and deep learning may be used to enhance the accuracy and/or speed of the metrology module.

[0015] **Figure 1** is a high-level schematic block diagram and illustration of a system **100** with a metrology module **101**, according to some embodiments of the invention. System

100 may comprise metrology module **101** associated with at least one computer processor(s) **102** and/or metrology module **101** comprising at least one, or some of computer processor(s) **102**.

[0016] Metrology module **101** may comprise, or be associated with one or more estimation model(s) **120**, which may be implemented on computer processor(s) **102** as part of metrology module **101** or associated therewith, e.g., as training or simulation module(s) that are used to derive estimation model(s) **120**. Estimation model(s) **120** may be configured to provide estimations of at least one metrology metric with respect to measurement data of sites on received wafers. Estimation model(s) **120** are derived by at least one machine learning algorithm **110** which is applied to calculated training data **105** in a training stage **115** that relates the at least one metrology metric to initial metrology measurements.

[0017] Metrology module **101** may be configured to calculate training data **105** concerning the metrology metric(s) from the initial metrology measurements, e.g., relating to multiple sites **85** in a plurality of fields **80** of one or more training wafer **70**; to apply machine learning algorithm(s) **110** to calculated training data **105** to derive estimation model **120** of the metrology metric(s); to derive measurement data **122** from images of sites on the received wafers, and to use estimation model **120** to provide estimations of the metrology metric(s) **124** with respect to measurement data **122**.

[0018] For example, the calculation of training data **105** may comprise using pairs of images **95** and 180°-rotated images **95** derived from sites **85** on at least one training wafer **70**. Training data **105** comprises at least one processed feature **96** (as derived data **96**) which is derived from each pair of images **95** with respect to each site **85**. For example, the processed feature(s) may comprise 1D (one-dimensional) kernels representing an average along a specified direction in respective images **95** and/or image transformation data comprising DCT (discrete cosine transform) or Fourier transform of respective images **95**.

[0019] In certain embodiments, machine learning algorithm(s) **110** may comprise any of Principal Component Regression, Support Vector Machines, Gradient Boosting and/or Neural Networks algorithms.

[0020] In certain embodiments, training data **105** may comprise, at least partly, raw images **95** derived from plurality of sites **85** on one or more training wafer(s) **70** as the initial

metrology measurements, and machine learning algorithm(s) **110** comprises at least one deep learning algorithm applying deep learning methods **150** directly to raw or processed images **95** as training data **105**.

[0021] In certain embodiments, metrology module **101** may be configured to derive at least one confidence score **130** that quantifies a similarity between measurement data **122** and training data **105** and to use derived confidence score(s) **130** as a confidence measure for the estimations of the at least one metrology metric. Metrology module **101** may be further configured to reiterate the estimation model derivation using additional calculated training data, e.g., in a re-training stage **140**, to re-train machine learning algorithm(s) **110**, in case confidence score(s) surpasses respective specified threshold(s). Alternatively, or complementarily, confidence score(s) **130** may be used to provide process variation indications **135** such as relating to various process errors.

[0022] **Figure 2** is a high-level flowchart illustrating a method **200**, according to some embodiments of the invention. The method stages may be carried out with respect to system **100** and/or metrology module **101** described above, which may optionally be configured to implement method **200**. Method **200** may be at least partially implemented by at least one computer processor (e.g., **102**), possibly in metrology module **101**. Certain embodiments comprise computer program products comprising a computer readable storage medium having computer readable program embodied therewith and configured to carry out the relevant stages of method **200**. Certain embodiments comprise target design files of respective targets designed by embodiments of method **200**. Method **200** may comprise the following stages, irrespective of their order.

[0023] Method **200** comprises calculating training data concerning at least one metrology metric from initial metrology measurements (stage **210**), applying at least one machine learning algorithm to the calculated training data (stage **220**) to derive an estimation model of the at least one metrology metric (stage **230**). For example, calculating training data **210** may comprise Calculating representation features as the training data (stage **215**) and/or using raw or detailed data (stage **217**), e.g., for deep learning procedures. Method **200** further comprises deriving measurement data from images of sites on received wafers (stage **232**), and using the estimation model to provide estimations of the at least one

metrology metric with respect to the measurement data (stage **235**) and optionally compensating for process errors using the derived estimation model(s) (stage **237**).

[0024] For example, method **200** may comprise carrying out the calculation of the training data using pairs of images and 180°-rotated images derived from a plurality of sites on at least one training wafer.

[0025] In certain embodiments, the training data may comprise at least one processed feature which is derived from each pair with respect to each site, the at least one processed feature comprises 1D (one-dimensional) representing an average along a specified direction in the respective images and/or image transformation data comprising DCT (discrete cosine transform) or Fourier transform of the respective images. Alternatively or complementarily the at least one processed feature may comprise any of various accuracy metrics derived from captured images.

[0026] In certain embodiments, the machine learning algorithm(s) may comprise at least one of: Principal Component Regression, Support Vector Machines, Gradient Boosting and/or Neural Networks algorithms.

[0027] In certain embodiments, the training data may comprise, at least partly, raw images derived from sites on the training wafer(s) as the initial metrology measurements, and the machine learning algorithm(s) may comprise at least one deep learning algorithm.

[0028] Method **200** may further comprise deriving at least one confidence score that quantifies a similarity between the measurement data and the training data and is used as a confidence measure for the estimations of the at least one metrology metric (stage **240**). Confidence score(s) may be used to indicate excessive process variation (stage **242**) and/or reiterating the estimation model derivation using additional calculated training data, to re-train the machine learning algorithm(s), in case one or more of the confidence score(s) surpasses respective specified threshold(s) (stage **245**).

[0029] For example, disclosed embodiments may comprise estimating TIS (tool induced shifts, mainly from optics-related inaccuracies and expressed by the difference between measurements rotated by 180° with respect to each other) and/or overlay as the metrology metric(s), e.g., estimation model(s) **120** may comprise computational model(s) that estimate TIS, possibly from single measurements **122** per site. Training data **105** may comprise a limited number of images **95** taken from multiple sites **85** with known TIS, e.g.,

including 180°-rotated images for these sites, namely using two measurements per site **85** for deriving training data **105**. Training data **105** may be derived with respect to various representation features such as 1D kernels representing the averages of a given dimension in 2D images **95**, DCT representations of image **95**, various metrics relating to images **95**, etc. Such features may help to gain more knowledge than is explicit in measured images **95**, while allowing for simple computations for training data **105** and metric estimations **124**, by reducing the relatively large pixel space to more compact representations. In certain embodiments, by creating feature-based model **120** on single wafer **70**, the TIS or other metrics may be estimated and compensated for, e.g., site by site in many similar (received) wafers measured on the same metrology tool (e.g., having metrology module **101**), thus increasing the quality of overlay and other metrology measurements with a negligible penalty in throughput.

[0030] It is noted that disclosed methods **200** and systems **100** may be used in optical metrology measurements to minimize TIS errors which are caused by imperfections in the measurement devices (e.g., due to telecentricity, lens aberrations, etc.) that may be manifested in different overlays (indications of the misalignment of two or more vertically consecutive layer patterns in a semiconductor wafer) between measurements taken on the same target at 0° and 180° azimuths (measured by rotating the wafer by 180°). Disclosed embodiments may at least statistically minimize the TIS errors across the wafer, as observed in the mean and standard deviation of the values across the wafer.

[0031] Confidence score(s) **130** may be used to score inputs such as measurements **122** with respect to the similarity between measurements **122** and training data **105**, to provide a confidence measure to estimated metric values **124** such as the TIS prediction. By monitoring confidence score **130**, process variations occurring in the production process may be indicated **135** and/or re-training of model **120** may be triggered **140** to cope with identified changes in the process. Various embodiments yield higher quality results while maintaining high throughput as opposed to current methods of reducing TIS discussed below. Disclosed systems **100** and methods **200** may be applied to minimize a range of errors in the semiconductor process analysis flow.

[0032] In certain embodiments, alternative or complementary deep learning machine learning algorithms **110** and corresponding mechanisms **150** may be applied to bypass

and/or complement feature calculation stage **215**. Measured images may be used as at least part of training data **105** and inputted directly into, e.g., a neural network architecture (as an example for machine learning algorithms), with TIS estimates as its output.

[0033] The inventors note that disclosed embodiments pioneer the use of machine learning algorithms for correcting mechanical and optical errors in overlay measurement in the semiconductor industry. Disclosed embodiments perform better than prior art systems and methods which require conducting each measurement twice (at 0° and 180° rotations of the target) to derive, e.g., TIS measurements and/or which optimize the hardware settings on a given set of sites and wafers and use the optimized values for all other sites and wafers. Advantageously, disclosed embodiments halve the measurement time (by using a single measurement instead of two, and also sparing the wafer movement time), improve measurement accuracy and increase the overall throughput (number of wafers processed per hour) greatly with respect to the former prior art approach, and are much more flexible, more accurate and less time-consuming with respect to the latter prior art approach (as hardware setting optimization is a very slow process, that cannot be carried out often and therefore can hardly be adjusted to changing conditions, and also provide interpolative results which may have low accuracy).

[0034] Aspects of the present invention are described above with reference to flowchart illustrations and/or portion diagrams of methods, apparatus (systems) and computer program products according to embodiments of the invention. It will be understood that each portion of the flowchart illustrations and/or portion diagrams, and combinations of portions in the flowchart illustrations and/or portion diagrams, can be implemented by computer program instructions. These computer program instructions may be provided to a processor of a general-purpose computer, special purpose computer, or other programmable data processing apparatus to produce a machine, such that the instructions, which execute via the processor of the computer or other programmable data processing apparatus, create means for implementing the functions/acts specified in the flowchart and/or portion diagram or portions thereof.

[0035] These computer program instructions may also be stored in a computer readable medium that can direct a computer, other programmable data processing apparatus, or other devices to function in a particular manner, such that the instructions stored in the computer

readable medium produce an article of manufacture including instructions which implement the function/act specified in the flowchart and/or portion diagram or portions thereof.

[0036] The computer program instructions may also be loaded onto a computer, other programmable data processing apparatus, or other devices to cause a series of operational steps to be performed on the computer, other programmable apparatus or other devices to produce a computer implemented process such that the instructions which execute on the computer or other programmable apparatus provide processes for implementing the functions/acts specified in the flowchart and/or portion diagram or portions thereof.

[0037] The aforementioned flowchart and diagrams illustrate the architecture, functionality, and operation of possible implementations of systems, methods and computer program products according to various embodiments of the present invention. In this regard, each portion in the flowchart or portion diagrams may represent a module, segment, or portion of code, which comprises one or more executable instructions for implementing the specified logical function(s). It should also be noted that, in some alternative implementations, the functions noted in the portion may occur out of the order noted in the figures. For example, two portions shown in succession may, in fact, be executed substantially concurrently, or the portions may sometimes be executed in the reverse order, depending upon the functionality involved. It will also be noted that each portion of the portion diagrams and/or flowchart illustration, and combinations of portions in the portion diagrams and/or flowchart illustration, can be implemented by special purpose hardware-based systems that perform the specified functions or acts, or combinations of special purpose hardware and computer instructions.

[0038] In the above description, an embodiment is an example or implementation of the invention. The various appearances of "one embodiment", "an embodiment", "certain embodiments" or "some embodiments" do not necessarily all refer to the same embodiments. Although various features of the invention may be described in the context of a single embodiment, the features may also be provided separately or in any suitable combination. Conversely, although the invention may be described herein in the context of separate embodiments for clarity, the invention may also be implemented in a single embodiment. Certain embodiments of the invention may include features from different

embodiments disclosed above, and certain embodiments may incorporate elements from other embodiments disclosed above. The disclosure of elements of the invention in the context of a specific embodiment is not to be taken as limiting their use in the specific embodiment alone. Furthermore, it is to be understood that the invention can be carried out or practiced in various ways and that the invention can be implemented in certain embodiments other than the ones outlined in the description above.

[0039] The invention is not limited to those diagrams or to the corresponding descriptions. For example, flow need not move through each illustrated box or state, or in exactly the same order as illustrated and described. Meanings of technical and scientific terms used herein are to be commonly understood as by one of ordinary skill in the art to which the invention belongs, unless otherwise defined. While the invention has been described with respect to a limited number of embodiments, these should not be construed as limitations on the scope of the invention, but rather as exemplifications of some of the preferred embodiments. Other possible variations, modifications, and applications are also within the scope of the invention. Accordingly, the scope of the invention should not be limited by what has thus far been described, but by the appended claims and their legal equivalents.

CLAIMS

What is claimed is:

1. A method comprising:
 - calculating training data concerning at least one metrology metric from initial metrology measurements,
 - applying at least one machine learning algorithm to the calculated training data to derive an estimation model of the at least one metrology metric,
 - deriving measurement data from images of sites on received wafers, and
 - using the estimation model to provide estimations of the at least one metrology metric with respect to the measurement data.
2. The method of claim 1, further comprising carrying out the calculation of the training data using pairs of images and 180°-rotated images derived from a plurality of sites on at least one training wafer.
3. The method of claim 1 or 2, wherein the training data comprises at least one processed feature which is derived from each pair with respect to each site, the at least one processed feature comprises 1D (one-dimensional) kernels representing an average along a specified direction in the respective images and/or image transformation data comprising DCT (discrete cosine transform) or Fourier transform of the respective images.
4. The method of any one of claims 1-3, wherein the at least one machine learning algorithm comprises at least one of: Principal Component Regression, Support Vector Machines, Gradient Boosting and/or Neural Networks algorithms.
5. The method of claim 1 or 2, wherein the training data comprises, at least partly, raw images derived from a plurality of sites on at least one training wafer as the initial metrology measurements, and the at least one machine learning algorithm comprises at least one deep learning algorithm.
6. The method of any one of claims 1-5, further comprising deriving at least one confidence score that quantifies a similarity between the measurement data and the training data and is used as a confidence measure for the estimations of the at least one metrology metric.

7. The method of claim 6, further comprising reiterating the estimation model derivation using additional calculated training data, to re-train the at least one machine learning algorithm, in case at least one confidence score surpasses at least one specified threshold.
8. The method of any one of claims 1-7, wherein at least one of: the calculating, the applying and the using is carried out by at least one computer processor.
9. A computer program product comprising a non-transitory computer readable storage medium having computer readable program embodied therewith, the computer readable program configured to carry out, at least partly, the method of any one of claims 1-7.
10. A metrology module comprising the computer program product of claim 9.
11. A metrology module comprising an estimation model, configured to provide estimations of at least one metrology metric with respect to measurement data of sites on received wafers,
wherein the estimation model is derived by at least one machine learning algorithm applied to calculated training data that relates the at least one metrology metric to initial metrology measurements.
12. The metrology module of claim 11, further comprising at least one computer processor that is configured to derive the estimation model.
13. The metrology module of claim 11 or 12, further configured to
 - calculate training data concerning the at least one metrology metric from the initial metrology measurements,
 - apply the at least one machine learning algorithm to the calculated training data to derive the estimation model of the at least one metrology metric,
 - derive the measurement data from images of the sites on the received wafers, and
 - use the estimation model to provide the estimations of the at least one metrology metric with respect to the measurement data.
14. The metrology module of any one of claims 11-13, further configured to carry out the calculation of the training data using pairs of images and 180°-rotated images derived from a plurality of sites on at least one training wafer, wherein the training data comprises at least one processed feature which is derived from each pair with respect

to each site, the at least one processed feature comprises 1D (one-dimensional) kernels representing an average along a specified direction in the respective images and/or image transformation data comprising DCT (discrete cosine transform) or Fourier transform of the respective images.

15. The metrology module of any one of claims 11-14, wherein the at least one machine learning algorithm comprises at least one of: Principal Component Regression, Support Vector Machines, Gradient Boosting and/or Neural Networks algorithms.
16. The metrology module of any one of claims 11-13, wherein the training data comprises, at least partly, raw images derived from a plurality of sites on at least one training wafer as the initial metrology measurements, and the at least one machine learning algorithm comprises at least one deep learning algorithm.
17. The metrology module of any one of claims 11-16, further configured to derive at least one confidence score that quantifies a similarity between the measurement data and the training data and use the derive at least one confidence score as a confidence measure for the estimations of the at least one metrology metric; wherein the metrology module is further configured to reiterate the estimation model derivation using additional calculated training data, to re-train the at least one machine learning algorithm, in case at least one confidence score surpasses at least one specified threshold.

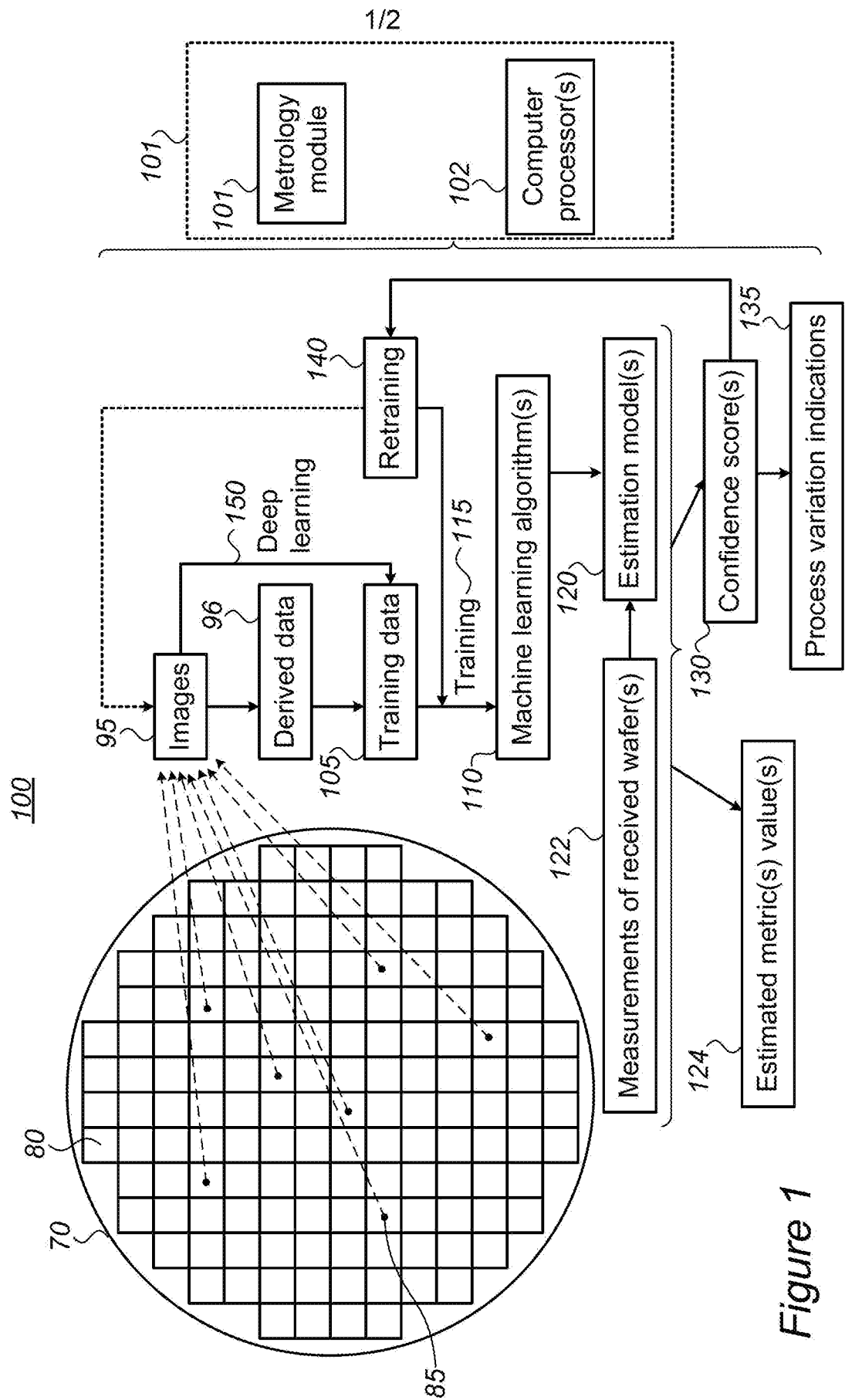
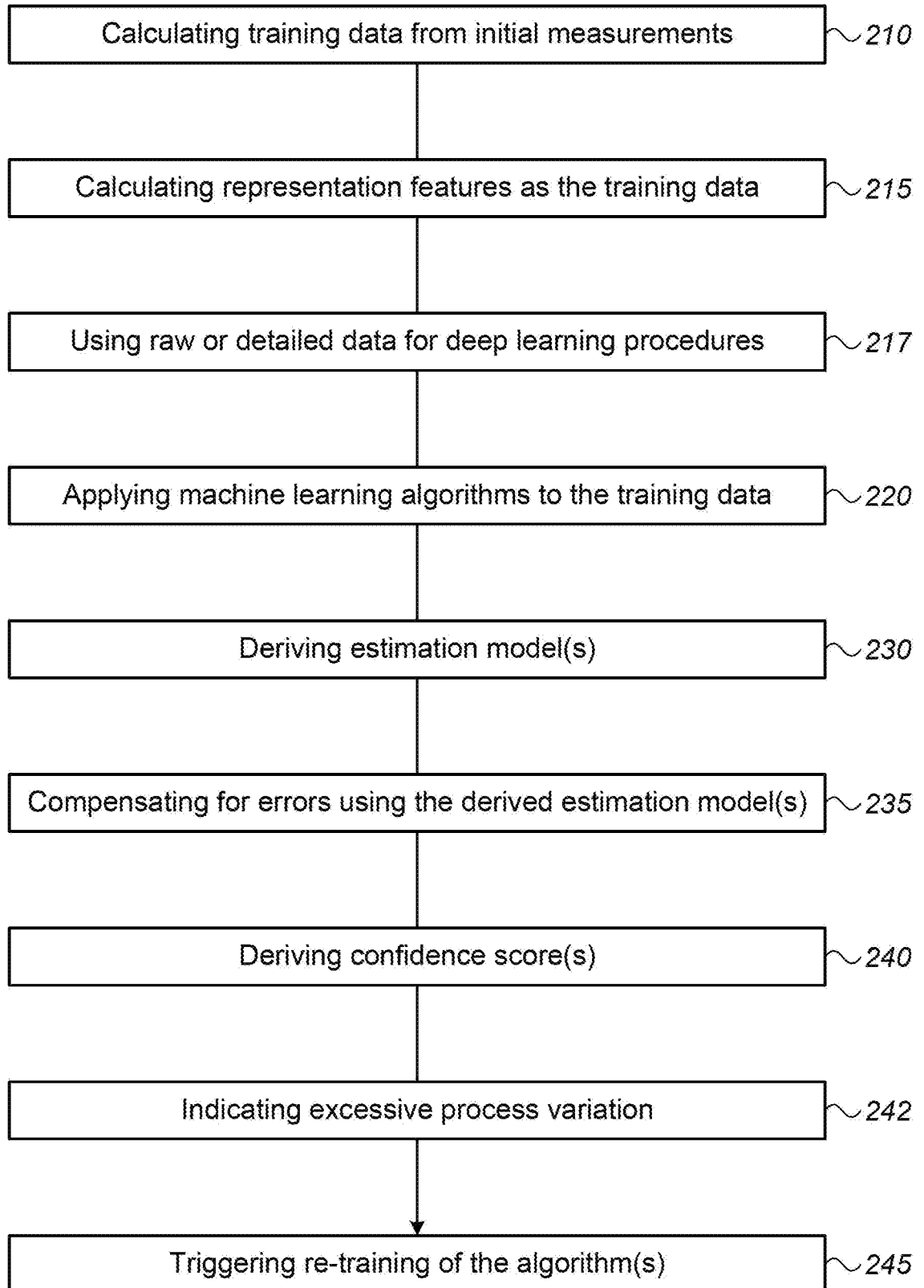


Figure 1

2/2

200*Figure 2*

A. CLASSIFICATION OF SUBJECT MATTER**G06N 20/10(2019.01)i, G06N 3/08(2006.01)i, G01N 21/88(2006.01)i, G01N 21/95(2006.01)i**

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

G06N 20/10; G01B 11/27; G06F 015/18; G06F 15/00; G06F 15/18; G06F 17/50; G06N 003/08; G06N 99/00; G06N 3/08; G01N 21/88; G01N 21/95

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Korean utility models and applications for utility models

Japanese utility models and applications for utility models

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

eKOMPASS(KIPO internal) & Keywords: training data, measurement data, metrology metric, estimation model, machine learning, wafers

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
Y	KR 10-2017-0085582 A (KLA-TENCOR CORPORATION) 24 July 2017 Paragraphs [0044]-[0047], [0064], [0077]; claim 1; and figures 2, 4	1-17
Y	US 2015-0323316 A1 (KLA-TENCOR CORPORATION) 12 November 2015 Paragraph [0047]; claim 1; and figure 1	1-17
Y	US 2004-0267397 A1 (SRINIVAS DODDI et al.) 30 December 2004 Paragraph [0057]; and figure 5	6-7, 17
A	US 7593912 B2 (FAN-TIEN CHENG et al.) 22 September 2009 Column 4, line 58 - column 5, line 55; claim 1; and figure 1	1-17
A	US 2017-0193400 A1 (KLA-TENCOR CORPORATION) 06 July 2017 Paragraphs [0029]-[0039]; claim 1; and figure 1	1-17



Further documents are listed in the continuation of Box C.



See patent family annex.

* Special categories of cited documents:

"A" document defining the general state of the art which is not considered to be of particular relevance

"D" document cited by the applicant in the international application

"E" earlier application or patent but published on or after the international filing date

"L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)

"O" document referring to an oral disclosure, use, exhibition or other means

"P" document published prior to the international filing date but later than the priority date claimed

"T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention

"X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone

"Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art

"&" document member of the same patent family

Date of the actual completion of the international search

24 April 2020 (24.04.2020)

Date of mailing of the international search report

24 April 2020 (24.04.2020)

Name and mailing address of the ISA/KR

International Application Division

Korean Intellectual Property Office

189 Cheongsa-ro, Seo-gu, Daejeon, 35208, Republic of Korea

Facsimile No. +82-42-481-8578

Authorized officer

KWON, Sungho

Telephone No. +82-42-481-3547



INTERNATIONAL SEARCH REPORT

Information on patent family members

International application No.

PCT/US2019/068219

Patent document cited in search report	Publication date	Patent family member(s)	Publication date
KR 10-2017-0085582 A	24/07/2017	CN 107077644 A IL 251416 A US 10152678 B2 US 2016-0141193 A1 WO 2016-081656 A1	18/08/2017 29/05/2017 11/12/2018 19/05/2016 26/05/2016
US 2015-0323316 A1	12/11/2015	CN 106463429 A CN 106463429 B IL 248105 D0 KR 10-2017-0005059 A TW 201546925 A TW I668774 B US 10352876 B2 WO 2015-172027 A1	22/02/2017 25/10/2019 30/11/2016 11/01/2017 16/12/2015 11/08/2019 16/07/2019 12/11/2015
US 2004-0267397 A1	30/12/2004	CN 100418083 C CN 1799045 A DE 112004001001 T5 JP 2007-528985 A JP 4589315 B2 KR 10-1059427 B1 KR 10-2006-0033740 A US 2009-0198635 A1 US 7831528 B2 WO 2005-003911 A2 WO 2005-003911 A3	10/09/2008 05/07/2006 14/09/2006 18/10/2007 01/12/2010 25/08/2011 19/04/2006 06/08/2009 09/11/2010 13/01/2005 30/06/2005
US 7593912 B2	22/09/2009	TW 200742951 A TW I315054 B US 2007-0282767 A1	16/11/2007 21/09/2009 06/12/2007
US 2017-0193400 A1	06/07/2017	CN 108431587 A CN 108475351 A EP 3397952 A1 EP 3397952 A4 EP 3398123 A1 EP 3398123 A4 IL 259705 D0 IL 259706 D0 JP 2019-508678 A JP 2019-508789 A KR 10-2018-0089911 A KR 10-2018-0090385 A TW 201734439 A TW 201734825 A US 2017-0194126 A1 US 9916965 B2 WO 2017-117568 A1 WO 2017-117573 A1	21/08/2018 31/08/2018 07/11/2018 28/08/2019 07/11/2018 28/08/2019 31/07/2018 31/07/2018 28/03/2019 28/03/2019 09/08/2018 10/08/2018 01/10/2017 01/10/2017 06/07/2017 13/03/2018 06/07/2017 06/07/2017